

# Evan A Clinton

## List of Publications by Year in descending order

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13  
papers

265  
citations

1040056

9  
h-index

1125743

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g-index

14  
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14  
docs citations

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times ranked

370  
citing authors

#	ARTICLE	IF	CITATIONS
1	Adlayer control for tunable AlGa <sub>N</sub> self-assembled superlattices. <i>Journal of Applied Physics</i> , 2021, 130, .	2.5	5
2	Thermal conductance across harmonic-matched epitaxial Al-sapphire heterointerfaces. <i>Communications Physics</i> , 2020, 3, .	5.3	41
3	Comprehensive Analysis of Metal Modulated Epitaxial GaN. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 37693-37712.	8.0	15
4	Beryllium doped semi-insulating GaN without surface accumulation for homoepitaxial high power devices. <i>Journal of Applied Physics</i> , 2020, 127, 215703.	2.5	13
5	Controlling surface adatom kinetics for improved structural and optical properties of high indium content aluminum indium nitride. <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	7
6	Observation and mitigation of RF-plasma-induced damage to III-nitrides grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2019, 126, .	2.5	9
7	Ultra-wide-bandgap AlGa <sub>N</sub> homojunction tunnel diodes with negative differential resistance. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	23
8	The role of Mg bulk hyper-doping and delta-doping in low-resistance GaN homojunction tunnel diodes with negative differential resistance. <i>Journal of Applied Physics</i> , 2019, 126, 083110.	2.5	7
9	Negative differential resistance in GaN homojunction tunnel diodes and low voltage loss tunnel contacts. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	27
10	InGa <sub>N</sub> solar cells with regrown GaN homojunction tunnel contacts. <i>Applied Physics Express</i> , 2018, 11, 082304.	2.4	22
11	A review of the synthesis of reduced defect density In <sub>x</sub> Ga <sub>1-x</sub> N for all indium compositions. <i>Solid-State Electronics</i> , 2017, 136, 3-11.	1.4	19
12	Control of ion content and nitrogen species using a mixed chemistry plasma for GaN grown at extremely high growth rates >9â€‰%<i>Î¼</i>m/h by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	28
13	Comprehensive study of the electronic and optical behavior of highly degenerate p-type Mg-doped GaN and AlGa <sub>N</sub> . <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	49